2SC4702

Silicon NPN Epitaxial

HITACHI

Application

High voltage amplifier

Features

• High breakdown voltage

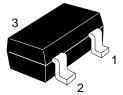
$$V_{\text{CEO}} = 300 \text{ V}$$

• Small Cob

$$Cob = 1.5 pF Typ.$$

Outline

MPAK



- 1. Emitter
- 2. Base
- 3. Collector



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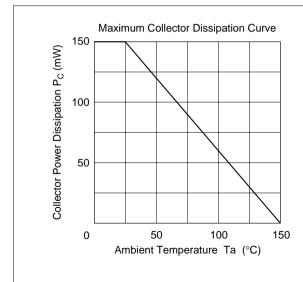
Absolute Maximum Ratings (Ta = 25°C)

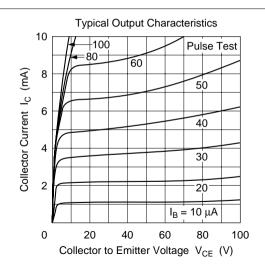
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	300	V
Collector to emitter voltage	V _{CEO}	300	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I _c	50	mA
Collector power dissipation	P _c	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

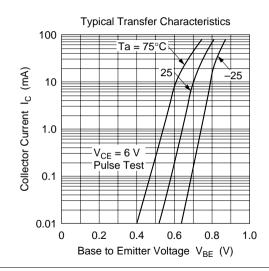
Electrical Characteristics (Ta = 25°C)

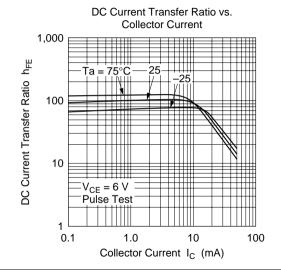
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	300	_	_	V	$I_{c} = 10 \ \mu\text{A}, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	300	_	_	V	$I_{C} = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_{E} = 10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	0.1	μΑ	$V_{CB} = 250 \text{ V}, I_{E} = 0$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	0.5	V	$I_C = 30 \text{ mA}, I_B = 3 \text{ mA}$
DC current transfer ratio	h _{FE}	60	_	150		$V_{CE} = 6 \text{ V}, I_{C} = 2 \text{ mA}$
Gain bandwidth product	f _T	_	80	_	MHz	$V_{CE} = 6 \text{ V}, I_{C} = 5 \text{ mA}$
Collector output capacitance	Cob	_	1.5	_	pF	V _{CB} = 10 V, I _E = 0, f = 1 MHz

Note: Marking is "XV-".

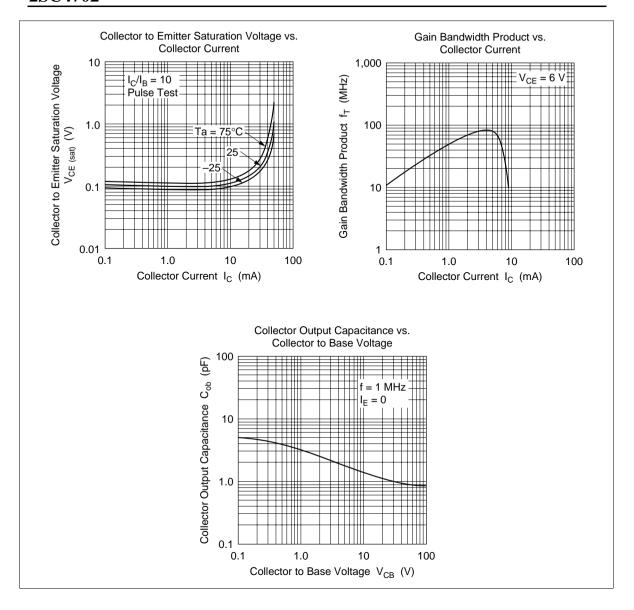




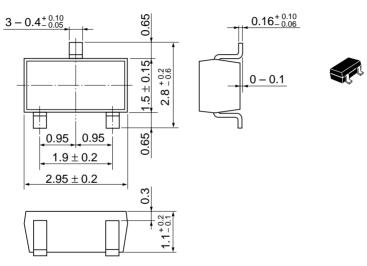




2SC4702



Unit: mm



Hitachi Code	MPAK
JEDEC	_
EIAJ	Conforms
Weight (reference value)	0.011 g

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